

PDFN3.3X3.3-8 P Channel Enhancement 沟道增强型 MOS Field Effect Transistor 场效应管

■Features 特点

Low on-resistance 低导通电阻

$R_{DS(ON)}=9m\Omega(\text{Type})@V_{GS}=-10V$

$R_{DS(ON)}=14.7m\Omega(\text{Type})@V_{GS}=-4.5V$

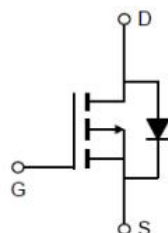
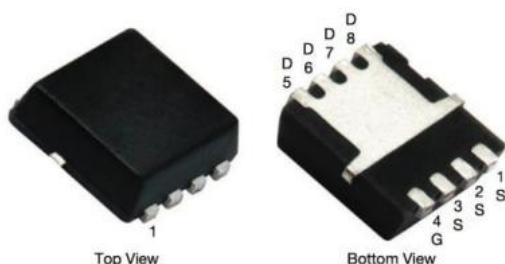
■Applications 应用

Backlight 背光驱动

DC-DC Conversion 升压转换

Power Management 电源管理

■Internal Schematic Diagram 内部结构



■Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Drain-Source Voltage 漏极-源极电压	BV_{DSS}	-30	V
Gate- Source Voltage 栅极-源极电压	V_{GS}	± 20	V
Drain Current (continuous)漏极电流-连续	I_D (at $T_C = 25^\circ C$ at $T_A = 25^\circ C$)	-44 -15	A
Drain Current (pulsed)漏极电流-脉冲	I_{DM}	-176	A
Total Device Dissipation 总耗散功率	P_{TOT} (at $T_C = 25^\circ C$ at $T_A = 25^\circ C$)	30 3.1	W
Avalanche Energy(Single Pulse)雪崩能量	E_{AS}	101	mJ
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JC}/R_{\theta JA}$	4.1/40	$^\circ C/W$
Junction/Storage Temperature 结温/储存温度	T_J, T_{stg}	-55~150	$^\circ C$

■ Electrical Characteristics 电特性

 (T_A=25℃ unless otherwise noted 如无特殊说明, 温度为 25℃)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压(I _D = -250uA, V _{GS} =0V)	BV _{DSS}	-30	—	—	V
Gate Threshold Voltage 栅极开启电压(I _D = -250uA, V _{GS} = V _{DS})	V _{GS(th)}	-1	-1.5	-3	V
Zero Gate Voltage Drain Current 零栅压漏极电流(V _{GS} =0V, V _{DS} = -30V)	I _{DSS}	—	—	-1	μA
Gate Body Leakage 栅极漏电流(V _{GS} =±20V, V _{DS} =0V)	I _{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance 静态漏源导通电阻(I _D = -15A, V _{GS} = -10V) (I _D = -10A, V _{GS} = -4.5V)	R _{DS(ON)}	—	9 14.7	14 20	mΩ
Diode Forward Voltage Drop 内附二极管正向压降(I _{SD} = -1A, V _{GS} =0V)	V _{SD}	—	-0.7	-1	V
Input Capacitance 输入电容 (V _{GS} =0V, V _{DS} = -15V, f=1MHz)	C _{ISS}	—	2147	—	pF
Common Source Output Capacitance 共源输出电容(V _{GS} =0V, V _{DS} = -15V, f=1MHz)	C _{OSS}	—	407	—	pF
Reverse Transfer Capacitance 反馈电容 (V _{GS} =0V, V _{DS} = -15V, f=1MHz)	C _{RSS}	—	358	—	pF
Total Gate Charge 栅极电荷密度 (V _{DS} = -15V, I _D = -11.5A, V _{GS} = -10V)	Q _g	—	51	—	nC
Gate Source Charge 栅源电荷密度 (V _{DS} = -15V, I _D = -11.5A, V _{GS} = -10V)	Q _{gs}	—	8	—	nC
Gate Drain Charge 栅漏电荷密度 (V _{DS} = -15V, I _D = -11.5A, V _{GS} = -10V)	Q _{gd}	—	15	—	nC
Turn-ON Delay Time 开启延迟时间 (V _{DS} = -15V I _D = -1A, R _{GEN} =6Ω, V _{GS} = -10V)	t _{d(on)}	—	8	—	ns
Turn-ON Rise Time 开启上升时间 (V _{DS} = -15V I _D = -1A, R _{GEN} =6Ω, V _{GS} = -10V)	t _r	—	20	—	ns
Turn-OFF Delay Time 关断延迟时间 (V _{DS} = -15V I _D = -1A, R _{GEN} =6Ω, V _{GS} = -10V)	t _{d(off)}	—	58	—	ns
Turn-OFF Fall Time 关断下降时间 (V _{DS} = -15V I _D = -1A, R _{GEN} =6Ω, V _{GS} = -10)	t _f	—	43	—	ns

■ Typical Characteristic Curve 典型特性曲线

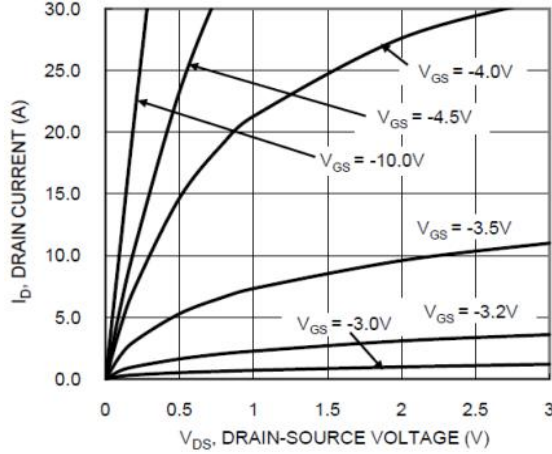


Figure 1: Output Characteristics

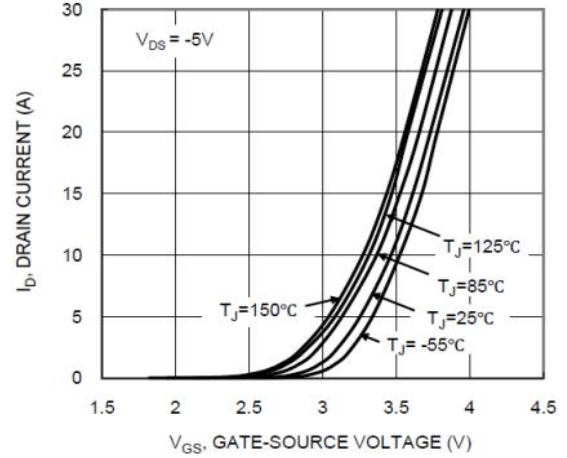


Figure 2: Transfer Characteristics

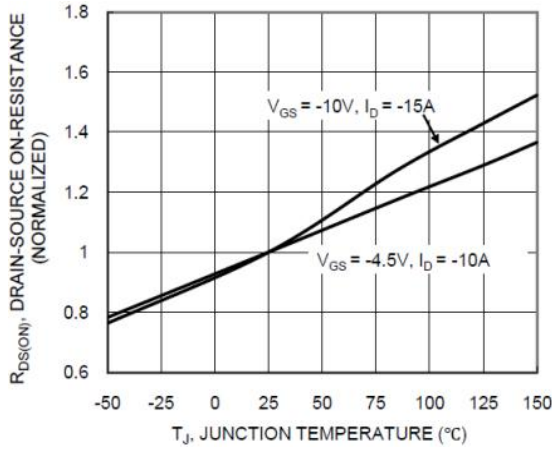


Figure 3: On-Resistance vs. T_J

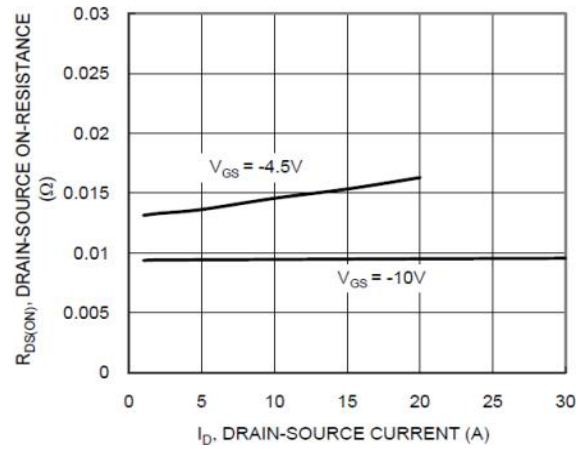


Figure 4: On-Resistance vs. Drain Current

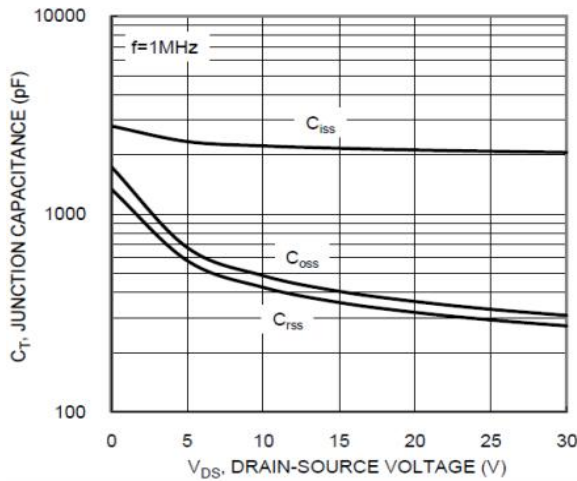


Figure 5: Capacitance Characteristics

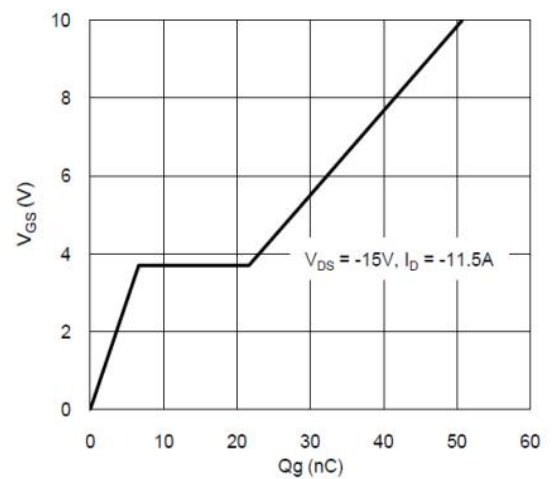


Figure 6: Gate-Charge Characteristics

■ Typical Characteristic Curve 典型特性曲线

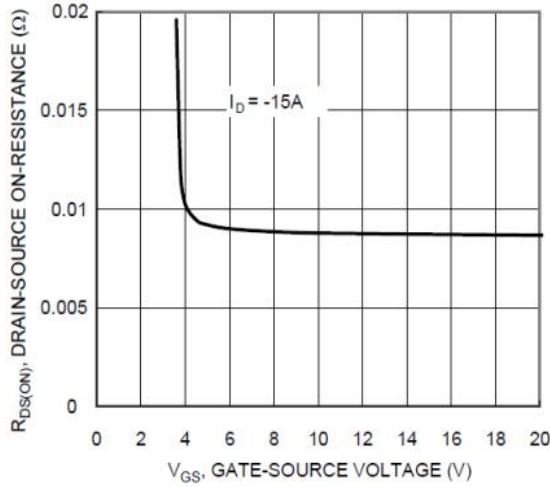


Figure 7: On-Resistance vs. V_{GS}

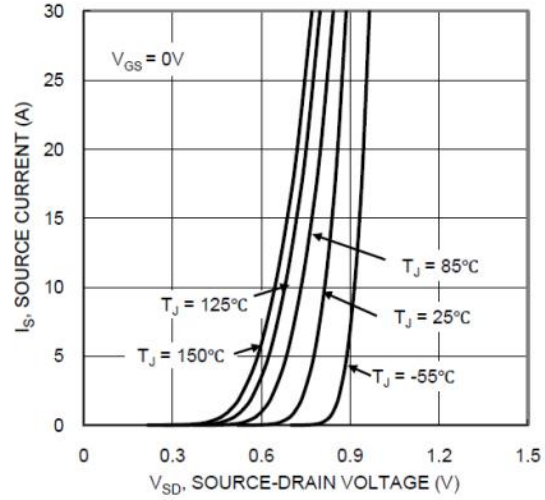


Figure 8: Diode Characteristics

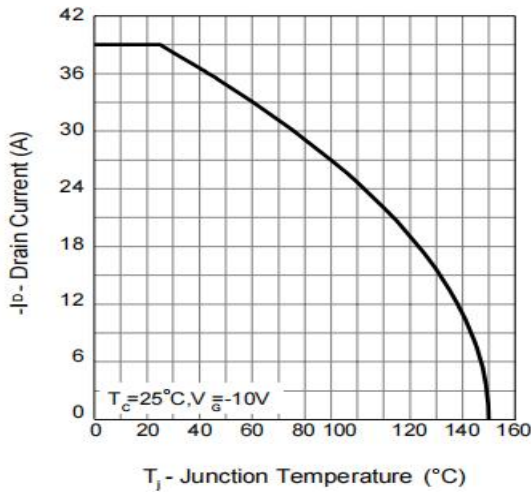


Figure 9: Drain Current Characteristics

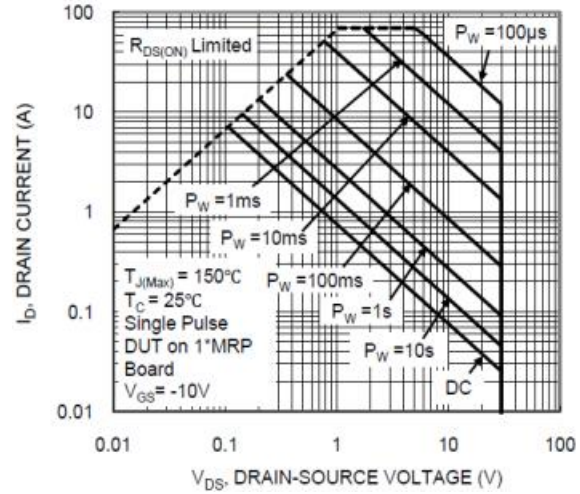


Figure 10: Safe Operating Area

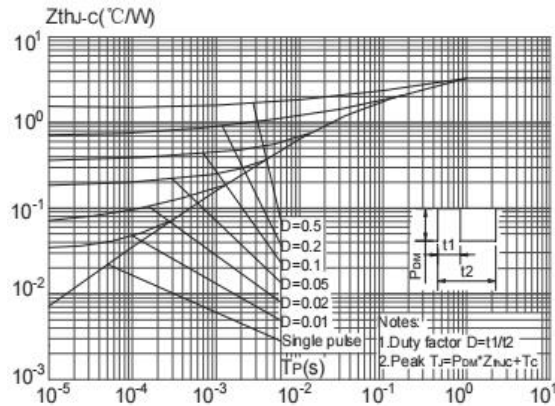
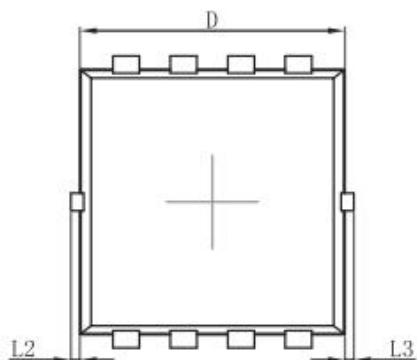
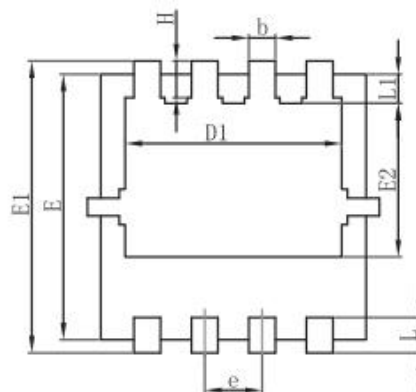


Figure 11: Transient Thermal Response Curve

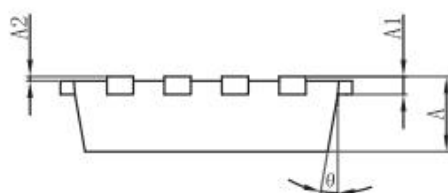
■ **Dimension 外形封装尺寸**



Top View



Bottom View



Side View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.650	0.850	0.026	0.033
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.900	3.100	0.114	0.122
D1	2.300	2.600	0.091	0.102
E	2.900	3.100	0.114	0.122
E1	3.150	3.450	0.124	0.136
E2	1.535	1.935	0.060	0.076
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.315	0.515	0.012	0.020
θ	9°	13°	9°	13°